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Nitrogen based magnetic semiconductors

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We describe a possible pathway to new magnetic materials with no conventional magnetic elements present. The substitution of Nitrogen for Oxygen in simple non magnetic oxides leads to holes in N $2p$ states which form local magnetic moments. Because of the very large Hund's rule coupling of Nitrogen and O $2p$ electrons and the rather extended spatial extend of the wave functions these materials are predicted to be ferromagnetic metals or small band gap insulators. Experimental studies support the theoretical calculations with regard to the basic electronic structure and the formation of local magnetic moments. It remains to be seen if these materials are magnetically ordered and if so below what temperature.

Since the discovery of ferromagnetism in Mn-doped GaAs[1] the study of magnetic impurities in non magnetic traditional semiconductors become a major trend in the field called diluted magnetic semiconductors (DMS). Recently it was proposed that oxides based DMS form another class of materials with promise for ferromagnetism at temperatures even higher than are currently achieved with III-IV semiconductors[2]. Following this prediction, several ZnO, and TiO_2, based systems have been reported to show ferromagnetism at room temperature if substituted with $3d$ elements[3, 4].

Nevertheless, in spite of accelerated interest in these materials, the exact mechanism responsible for the observed magnetic properties continues to be strongly debated in the literature. Several studies reported strong evidence of phase separation and formation of ferromagnetic clusters suggesting a non intrinsic behavior not suitable for technological applications. In addition, some of ZnO:Mn and Co-doped systems were reported to show only paramagnetic rather than ferromagnetic properties[5, 6, 7, 8]. It is believed that additional hole doping is needed to stabilize the ferromagnetic ground state in such DMS[9, 10]. Note that simple substitution of Mn^{2+} for divalent Zn in ZnO, for example, does not generate any extra carriers in itself. This is in contrast to Mn-doped GaAs where Mn introduces one hole per substituted cation. The interaction between these holes and electrons in $3d$ impurity states is one of the critical elements in the physics of diluted magnetic semiconductors[2, 11, 12].

Another important factor is the strong Hund's rule coupling J_H that favors a high-spin configuration on the impurity site. Note that the large splitting between occupied spin up and unoccupied spin down states in Mn^{2+} impurities is only partially due to the Coulomb repulsion U which is actually strongly reduced in a solid. J_H, on the other hand, is hardly reduced from its atomic value of about 0.9eV per spin pair on average for the series of $3d$ TM's[13, 14]. In this context, it is worthwhile to note that strong effective Hund's rule coupling between the carriers bound to vacancies was recently proposed as another way to introduce magnetism in none magnetic semiconductors[15].

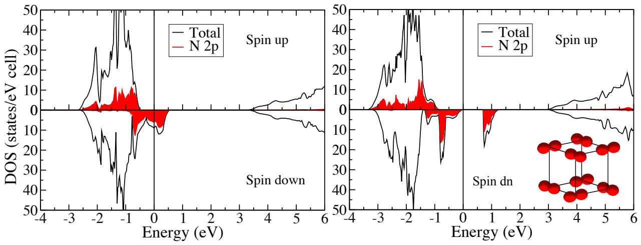

FIG. 1: Total and Nitrogen $2p$ partial densities of states calculated in LSDA (left panel) and LSDA+U (right panel) for 25% N substitution. LSDA+U density of states is calculated with U^{N2p}=U^{O2p}=4.6eV, and J_H^{N2p}=J_H^{O2p}=1.2eV. The zero of energy is at Fermi energy.

Using cation vacancy in CaO as an example, it was shown that two holes in otherwise full Oxygen $2p$ orbitals on the nearest neighbor sites of the vacancy sites form a stable magnetic (spin triplet) ground state in a simple, originally non magnetic band insulator. Note that even at very small concentrations such charge compensating clusters have significant overlap due to the extended nature of these objects. The origin of such strong coupling is, however, in the kinetic energy and symmetry of the molecular orbitals rather than in local, on-site interactions.

Aside from this it is illuminating to realize that the lowest energy configuration for two holes in $2p$ orbitals of atomic O or N is a spin triplet (^{3}P) configuration and the energy required to reach the first exited, spin singlet ^{1}D, is 0.13Ry in the case of atomic O[16]. This corresponds

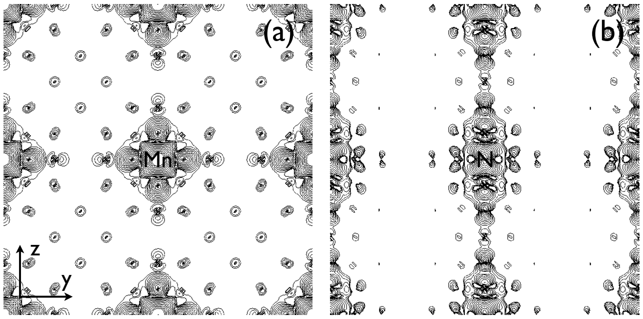

FIG. 2: LSDA+U spin density calculated for 0.9% Mn (a) and Nitrogen (b) substitution in SrO with U^{N2p}=U^{O2p}=4.6eV, J_H^{N2p}=J_H^{O2p}=1.2eV, U^{Mn3d}=2.34eV and J_H^{Mn3d}=0.89eV. Shown is a cut in (100) plane of 6x6 super cell. Note that charge-compensating hole resides in the Nitrogen p_z orbital. Lattice sites are not shown for clarity.

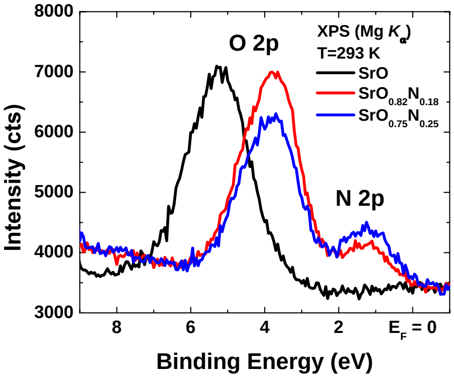

FIG. 3: Room temperature XPS valence band spectra of $SrO_{1-x}N_x$ films. The zero of binding energy is at Fermi level of Copper.

to 1.47eV for J_H. Note that the Hartree-Fock value of J_H for $3d$ electrons in Cu, for example, is 1.45eV[13]. This demonstrates that there is no reason why a system with holes in anion p bands could not be magnetic provided the band width is not too large.

Auger spectroscopy studies of simple oxides show that F^0 integral for two holes in an O $2p$ orbital is 4-7 eV[17, 18]. Note that with Auger spectroscopy of otherwise boring oxides one can determine the energies of the final states with two holes on an Oxygen ion. In fact it turns out that because of Auger matrix elements only the two singlet states can be reached being the singlet ^1S and the ^1D state whose energy splitting determines F^2[19, 20]. In the case of Cu_2O the F^2 integral is found to be 6eV that corresponds to 1.2eV for J_H[21, 22].

In spite of such striking similarities, there are several important difference between TM $3d$ orbitals and Oxygen $2p$ in oxides. First the the Oxygen $2p$ bands are usually full in ionic oxides leaving no room for unpaired spins. Even in the hole doped cuprates the density of O holes is small so that the effect of this Hund's rule coupling will be rather small. An interesting exception is CrO_2 in which Oxygen based bands cross the Fermi energy and indeed there is unpaired spin density in O[23]. Secondly the much larger spatial extend of the O $2p$ orbitals which could facilitate longer range exchange interactions. Note that d-d hopping integrals (t_{dd}) scale as the inverse of the fifth power of inter-atomic distance whereas $t_{pp} \sim 1/r^2$[24]. The consequence of this is two fold. First the larger spatial extend will cause large band widths which will compete with the tendency towards ferromagnetism. This would point in a direction of larger lattice constants such as is the case in SrO when comparing to the $3d$ transition metal oxides. Secondly the larger hopping integrals will cause more delocalization over neighboring atoms resulting in longer range exchange interactions. The first is unfavorable but the second favorable. To get a win-win situation in which both effects favor ferromagnetism we suggested the use of N substitution for O. N^{2-} has one less electron and because of the lower binding energy the N $2p$ states will be closer to the chemical potential than the O $2p$ states forming a relatively narrow impurity band with one hole per N situated just above the chemical potential. We note that such a substitution has recently been discussed in the context of ferromagnetism in Mn-doped ZnO, for example, where it is used to increase the ferromagnetic coupling between Mn impurities[9, 10]. In the present paper we present theoretical and experimental evidence that substitution of Nitrogen for Oxygen in simple band insulators such as SrO is, in itself, sufficient to produce DMS. This reveals a whole class of new materials whose magnetic properties are determined solely by the interaction between the carriers in p rather than d or f atomic shells.

As many other divalent oxides, SrO has the rock salt crystal structure with a lattice constant of 5.16Å. Pure SrO is a nonmagnetic band insulator with a forbidden gap of 5.3eV. The LDA-calculated gap is 3.9eV. In contrast to TM in III-V semiconductors, Nitrogen substitution in oxides can be substantially higher provided that one uses molecular beam epitaxy (MBE) methods to introduce N. For example, Voogt *et al* reported that NO_2-assisted MBE growth of FeO resulted in thin films with a rock salt crystal structure where up to 18% of anion sites were occupied by Nitrogen[26]. It is, therefore, interesting to investigate the effect of high Nitrogen concentration on the properties of $SrO_{1-x}N_x$.

Fig.1 shows the total and N $2p$ partial density of states calculated for 25% Nitrogen substitution with TB-LMTO computer code[27] within the local spin density approximation (LSDA). As in the case of low N concentration, LSDA predicts a ferromagnetic metallic ground state. However, it is well known that LSDA usually fails to describe strongly correlated systems adequately. In order to account for correlation effects we performed LSDA+U calculation[28] with U^{N2p}=U^{O2p}=4.6eV, and

J_H^{N2p}=J_H^{O2p}=1.2eV. It is found that SrO$_{0.75}$N$_{0.25}$ is, in fact a semiconductor with an energy gap of 0.7eV in ferromagnetic spin arrangement (Fig.1) and 1.1eV in antiferromagnetic one. In addition, the ferromagnetic solution becomes metallic if U is less than 3.3 eV whereas decreasing J_H from 1.2 to 0.5eV in fact increases the gap by 0.3eV. Note, however, that orbital degeneracy is lifted via the mechanism of orbital ordering which is actually frustrated if Nitrogen is distributed over the lattice in the periodic fashion such as in a simple cubic superstructure. One possible hole-density configuration, which corresponds to the calculated ferromagnetic density of states, is shown in the inset of Fig.1. We also note that, similar to manganites, spin and orbital degrees of freedom in these materials are strongly correlated which influences drastically the low energy properties. Although, ferromagnetic and A-type antiferromagnetic solutions are degenerate within our computational approach (the total energy difference between former and latter is 1meV), the G-type is 0.19eV higher in energy due to transition from antiferro to ferro orbital ordering. This, of course is very sensitive to lattice spacing, crystal structure distortion and morphology of the actual material. It is, therefore, really important to address these issues from an experimental point of view.

To demonstrate the difference in the spatial extend of the induced spin density between transition metal and ligand substitutions we compare first principle density functional calculation of 0.9% Mn and N substituted in SrO. Within the bounds of LSDA+U approach, both systems are magnetic and insulating with the moment of 5 and 1μ_B per supercell, respectively. We note that our LSDA calculations based on the supercell approximation agree with coherent potential approximation results [25]. The LSDA+U calculations of Mn doped SrO were performed with U^{Mn3d}=2.34eV and J_H^{Mn3d}=0.89eV [13]. The values of U and J for O 2p were 4.6 and 1.2eV, respectively. As one can see from Fig.2, the spin density due to Mn is highly concentrated around the first nearest Oxygen neighbors whereas for Nitrogen it is spread out over several neighboring shells and it is rather directional. This, of course, directly follows from the spatial and angular dependences of the hopping parameters for 2p in comparison to 3d orbitals.

We tried to prepare SrO$_{1-x}$N$_x$ by solid state chemistry methods using powders of SrN and SrO but found in the end only phase separated materials or Sr Nitroxides. However as mentioned above it is documented that Fe Oxides contain substitutional Nitrogen if grown by MBE methods using NO as the oxidizing gas. This suggests that the lower temperatures used in MBE growth together with the fact that only surface and not bulk diffusion is needed for layer by layer growth results in metastable materials with substitutional N. We note that this may be of general importance in other new systems such as phosphorous substituted sulfides etc.

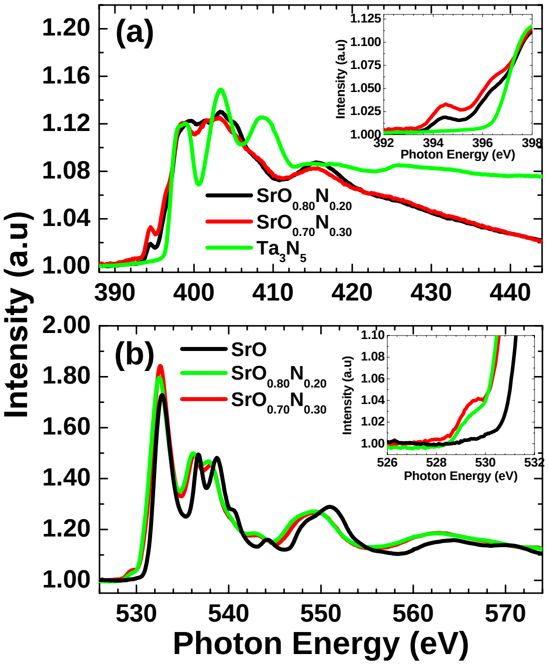

FIG. 4: Room temperature x-ray absorption spectra with E⊥c of SrO$_{1-x}$N$_x$ films, taken in the total electron yield mode at the Nitrogen (a) and Oxygen (b) K-edges. Note pre-edge structure at 394.5eV in (a) and 529.25eV in (b).

Films were grown epitaxial on MgO (100) single crystal under Ultra High Vacuum (UHV) conditions[29]. In order to produce films of high quality we use Molecular Beam Epitaxy (MBE). Reflection High Energy Diffraction (RHEED) was used to monitor the growth process. The periodic oscillations observed in the specular spot intensity of the high-energy electron beam reflected from the film surface are evidence for a layer-by-layer type of growth. Films with various concentrations of N were grown using NO gas as an oxidizing agent. The structure of the films was proven to be the same as the substrate (FCC), although (due to a large lattice mismatch) after several layers, having a different in-plane lattice constant then the substrate. This in plane lattice constant turned out to be also dependent on N concentration, namely increasing with increasing N content. Good Low Energy Electron Diffraction (LEED) image also confirms the high quality of the films. A more detailed description of the growth will be given elsewhere.

The composition of the films was checked by in situ measurements of X-Ray Photoemission Spectroscopy (XPS). In Fig.3 we show XPS spectra taken at room temperature on samples with 0%, 18% and 25% Nitrogen. In agreement with the results of band structure calculations the N 2p peak is found to be about 2eV lower in binding energy relative to the position of O 2p peak. The relative change in intensity of these two peaks upon doping strongly indicates that the growth process is indeed a process of substitution. This is also supported by RHEED and LEED data. Note that the shift of the O $2p$ peak towards higher binding energy in the pure SrO originates from charging problems common for insulators[30]. A much smaller shift, if any, found in the samples containing Nitrogen is an indication of semiconducting or even metallic behavior.

X-ray Absorption Spectroscopy (XAS) measurements performed on NSRRC Dragon Beamline in Taiwan confirm our XPS results. This experiment was carried out with the incident beam polarization parallel to the sample surface (001 surface of MgO and $SrO_{1-x}N_x$). In Fig.4 we show XAS spectra taken in the total electron yield mode at the Nitrogen and Oxygen K-edges. The strong pre-peak at the N K-edge strongly supports the existence of N $2p$ holes. The presence of a weaker O pre-edge structure supports the suggestion of delocalization of the N $2p$ hole states onto neighboring O. Note that neither Ta_3N_5 nor SrO has such a feature in their K-edge spectra.

Nitrogen $1s$ core-level XPS was used to examine the degree of charge and spin localization. If charge-compensating holes reside primarily in the Nitrogen $2p$ orbitals, the spectra of $SrO_{1-x}N_x$ films should be similar to one found in gas phase NO with a double peak structure due to the exchange coupling of the unpaired $2p$ spin with the core-hole. If all other interactions are frozen out then the intensity ratio between a triplet (lower binding energy) and singlet (higher binding energy) peaks should be 3:1. Of course, in the real material this is often not the case and it is rather common that experimental ratio is large[31]. We find that in the $SrO_{0.75}N_{0.25}$ sample the ratio is 4:1 (Fig.5). The observed energy separation between singlet and triplet peaks is 1.6eV which is consistent with 1.5eV found in NO which has a spin of 1/2 localized mainly on N.

In conclusion, our experimental and theoretical results show that substitution of Nitrogen for Oxygen in simple nonmagnetic and insulating oxide results in a dramatic change of the electronic and magnetic properties. This opens a path to the new class of magnetic semiconductors whose properties are solely determined by the interactions between the holes in ligand p-orbitals.

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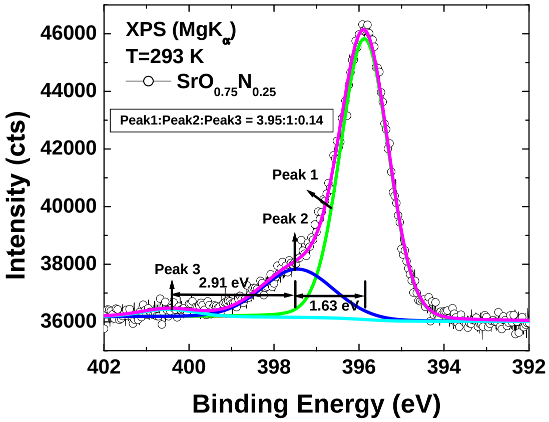

FIG. 5: Room temperature N $1s$ core-level XPS spectra of $SrO_{1-x}N_x$ film with x 0.25. The three peaks structure is due to a local spin 1/2 moment.

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